

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

Claims 1-14 are canceled.

15.(currently amended)      A spin valve type magnetoresistive read element for reading high recorded density, high RPM magnetic disks, ~~comprising~~ having a spin valve sensor element with abutted junctions upon which is formed a laminated longitudinal bias layer of hard magnetic material having high coercivity and squareness, and upon which is formed a laminated conducting lead layer of high sheet conductivity, high hardness, high melting point, high corrosion resistance and lacking the propensity for smearing, oozing, electromigration and nodule formation comprising:

a substrate;

a spin valve type sensor element formed on said substrate;

a laminated hard magnetic underlayer comprising a Ta/Cr seed layer upon which is formed a layer of hard magnetic material formed on said sensor element;

an "interrupt" layer formed on said underlayer, said interrupt layer having an amorphous structure and orienting the crystal plane of a subsequently formed layer;

a conductive lead layer, ~~laminated so as to provide specular reflection of conduction electrons and~~ formed over said "interrupt" layer and having its crystalline

axes oriented thereby, wherein the conducting lead layer is a three layer lamination consisting of a first layer of NiCr, upon which is formed a layer of conducting material, upon which is formed a second layer of NiCr, the interfaces between the NiCr and the conducting material causing specular reflection of conduction electrons so as to enhance the sheet conductivity of the formation.

16.(currently amended)      The structure of claim 15 wherein, within the laminated hard magnetic underlayer ~~comprises a seed double layer of Ta/Cr, the thickness of the Ta layer being preferably 50 A, but which could be~~ is in the range between 30 A and 75 A, the thickness of the Cr layer ~~is being preferably 100 A, but which could be~~ between 50 A and 150 A, ~~upon which Ta/Cr seed layer a~~ and said layer of hard magnetic material ~~such as is a layer of CoPtCr or CoPt, is formed to a thickness between approximately 150 A and 500 A.~~

Claims 17-18 are canceled.

19.(currently amended)      The structure of claim 18 wherein the "interrupt" layer is a layer of Ta, ~~preferably formed to a thickness of 50 A, but which could have~~ having a thickness of between 30 A and 75 A.

Claims 20-21 are canceled.

22.(currently amended)      The structure of claim 20 wherein the first layer of NiCr is preferably formed to a thickness of 50 A, ~~but which could be~~ in a range between 30 A and 75 A, the layer of conducting material is a layer of Ru, formed to a thickness of between 250 A and 520 A and the second layer of NiCr is ~~preferably~~ formed to a thickness of 50 A, ~~but which could be~~ in a range between 30 A and 50 A.

Claims 23-38 are canceled.